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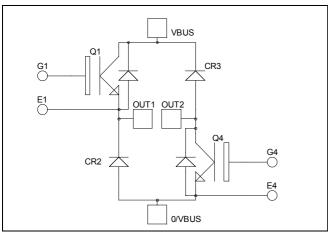






Asymmetrical - Bridge Trench + Field Stop IGBT3 Power Module





Application

- Welding converters
- Switched Mode Power Supplies
- Switched Reluctance Motor Drives

Features

- Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
 - M5 power connectors
- High level of integration

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- **RoHS Compliant**

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage		600	V
I_{C}	Continuous Collector Current	$T_C = 25^{\circ}C$	290	
	Continuous Conector Current	$T_C = 80$ °C	200	A
I_{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	400	
V_{GE}	Gate – Emitter Voltage		±20	V
P_{D}	Maximum Power Dissipation	$T_C = 25$ °C	625	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^{\circ}C$	400A @ 550V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25$ °C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I _{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$				250	μΑ
V _{CE(sat)}	Collector Emitter Saturation Voltage	$V_{GE} = 15V$ $I_{C} = 200A$	$T_j = 25$ °C		1.5	1.9	V
			$T_j = 150$ °C		1.7		·
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 2 \text{ mA}$		5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

Dynamic Characteristics

·	Characteristic	Test Conditions		Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$ $f = 1MHz$			12.3		nF
C_{oes}	Output Capacitance				0.8		
C_{res}	Reverse Transfer Capacitance				0.4		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)			115		
T_{r}	Rise Time	$V_{GE} = \pm 15V$			45		
$T_{d(off)}$	Turn-off Delay Time	$V_{\text{Bus}} = 300V$ $I_{\text{C}} = 200A$ $R_{\text{G}} = 2\Omega$			225		ns
$T_{\rm f}$	Fall Time				55		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_{C} = 200A$ $R_{G} = 2\Omega$			130		ns
$T_{\rm r}$	Rise Time				50		
$T_{d(off)}$	Turn-off Delay Time				300		
$T_{\rm f}$	Fall Time				70		
Б	Т	$V_{GE} = \pm 15V$	$T_j = 25$ °C		1		T
E _{on}	Turn on Energy	$V_{\text{Bus}} = 300 \text{V}$	$T_{j} = 150^{\circ}C$		1.8		mJ
F	Turn off Energy	$I_{\rm C} = 200 {\rm A}$	$T_j = 25$ °C		5.7		mJ
Loff	E _{off} Turn off Energy	$R_G = 2\Omega$ $T_j = 150^{\circ}C$		7		1113	

Diode ratings and characteristics

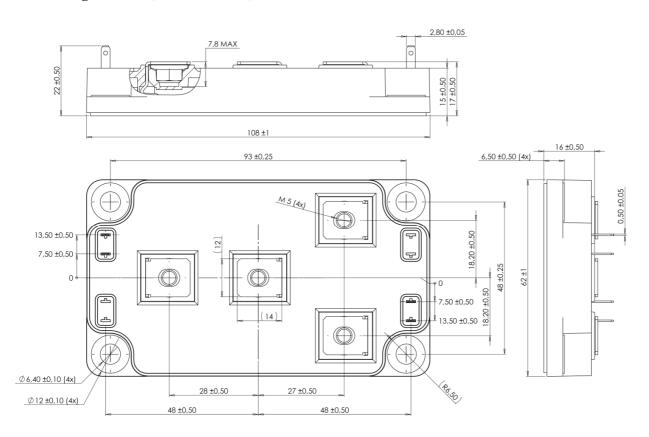
Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I_{RM}	Maximum Reverse Leakage Current	$V_R=600V$	$T_i = 25^{\circ}C$			250	μΑ
I_{F}	DC Forward Current		$T_{j} = 150^{\circ}C$ $Tc = 80^{\circ}C$		200	500	A
W	Diode Forward Voltage	$I_F = 200A$ $V_{GE} = 0V$	$T_i = 25^{\circ}C$		1.6	2	V
V_{F}			$T_{i} = 150^{\circ}C$		1.5		v
t	Reverse Recovery Time	$I_F = 200A$ $V_R = 300V$ $di/dt = 2200A/us$	$T_j = 25$ °C		130		ns
t_{rr}			$T_j = 150$ °C		225		115
0	Reverse Recovery Charge		$T_j = 25$ °C		9		C
Q_{rr}			$T_{i} = 150^{\circ}C$		19		μC
Г.,	D D E	1	$T_j = 25$ °C		2.3		I
Er	Reverse Recovery Energy		$T_i = 150^{\circ}C$		4.7		mJ



Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
R_{thJC}	L Junction to Case Thermal Resistance		IGBT			0.24	°C/W
			Diode			0.4	C/ W
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T_{J}	Operating junction temperature range			-40		175	
T_{STG}	Storage Temperature Range			-40		125	°C
$T_{\rm C}$	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
		For terminals	M5	2		3.5	18.111
Wt	Package Weight	•				300	g

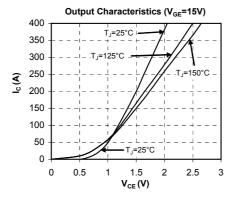
SP6 Package outline (dimensions in mm)

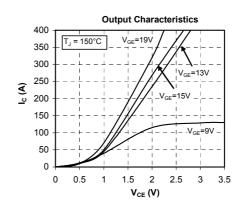


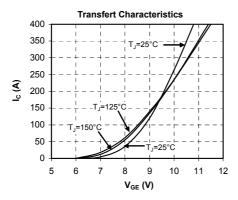
See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

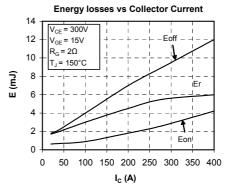


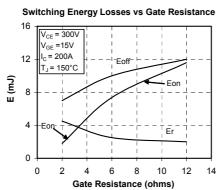
Typical Performance Curve

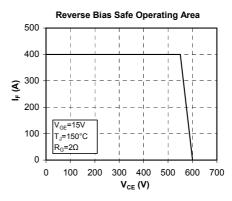


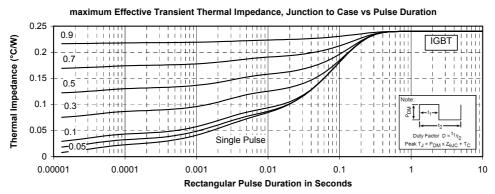






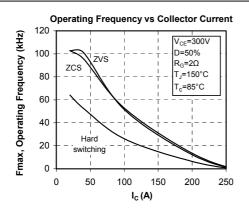


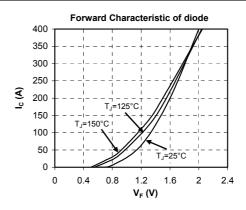


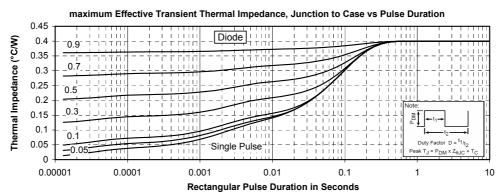


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